

IGBT

TRENCHSTOP™ IGBT3 Chip
SIGC32T120R3E

Data Sheet

Industrial Power Control



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TRENCHSTOP™ IGBT3 Chip

Features:

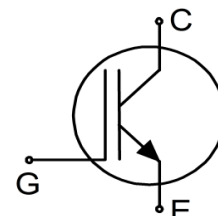
- 1200V trench & field stop technology
- Low turn-off losses
- Short tail current
- Positive temperature coefficient
- Easy paralleling

Recommended for:

- Power modules

Applications:

- Drives



Chip Type	V _{CE}	I _{CN} ¹	Die Size	Package
SIGC32T120R3E	1200V	25A	6.5mm x 4.87mm	Sawn on foil

Mechanical Parameters

Die size	6.5 x 4.87		mm ²
Emitter pad size	See chip drawing		
Gate pad size	1.139 x 1.139		
Area total	31.66		
Thickness	140		µm
Wafer size	200		mm
Maximum possible chips per wafer	842		
Passivation frontside	Photoimide		
Pad metal	3200nm AlSiCu		
Backside metal	Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process		
Die bond	Electrically conductive epoxy glue and soft solder		
Wire bond	Al, ≤500µm		
Reject ink dot size	Ø 0.65mm; max. 1.2mm		
Storage environment (<6 months)	for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C	
	for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.	

¹ Nominal collector current at T_C=100°C for chip packaged in power modules, see application example cited on page 5.

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj}=25^{\circ}\text{C}$	V_{CE}	1200	V
DC collector current, limited by $T_{vj\max}^2$	I_C	-	A
Pulsed collector current, t_p limited by $T_{vj\max}^3$	$I_{C,puls}$	75	A
Gate-emitter voltage	V_{GE}	± 20	V
Junction temperature range	T_{vj}	-40 ... +175	$^{\circ}\text{C}$
Operating junction temperature	T_{vj}	-40 ... +150	$^{\circ}\text{C}$
Short circuit data ^{3/4} $V_{GE}=15\text{V}$, $V_{CC}=900\text{V}$, $T_{vj}=150^{\circ}\text{C}$	t_{sc}	10	μs
Reverse bias safe operating area ³ (RBSOA)	$I_{C,max}=50\text{A}$, $V_{CE,max}=1200\text{V}$, $T_{vj}\leq 150^{\circ}\text{C}$		

Static Characteristics (tested on wafer), $T_{vj}=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}$, $I_C=1\text{mA}$	1200	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE}=15\text{V}$, $I_C=25\text{A}$	1.4	1.7	2.1	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=1\text{mA}$, $V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200\text{V}$, $V_{GE}=0\text{V}$	-	-	3.48	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0\text{V}$, $V_{GE}=20\text{V}$	-	-	600	nA
Integrated gate resistor	r_G		8			Ω

Electrical Characteristics ³

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE}=15\text{V}$, $I_C=25\text{A}$, $T_{vj}=125^{\circ}\text{C}$	-	2.0	-	V
Input capacitance	C_{ies}	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=1\text{MHz}$, $T_{vj}=25^{\circ}\text{C}$	-	1808	-	pF
Output capacitance	C_{oes}		-	95	-	
Reverse transfer capacitance	C_{res}		-	82	-	

² Depending on thermal properties of assembly.

³ Not subject to production test - verified by design/characterization.

⁴ Allowed number of short circuits: <1000; time between short circuits: >1s.



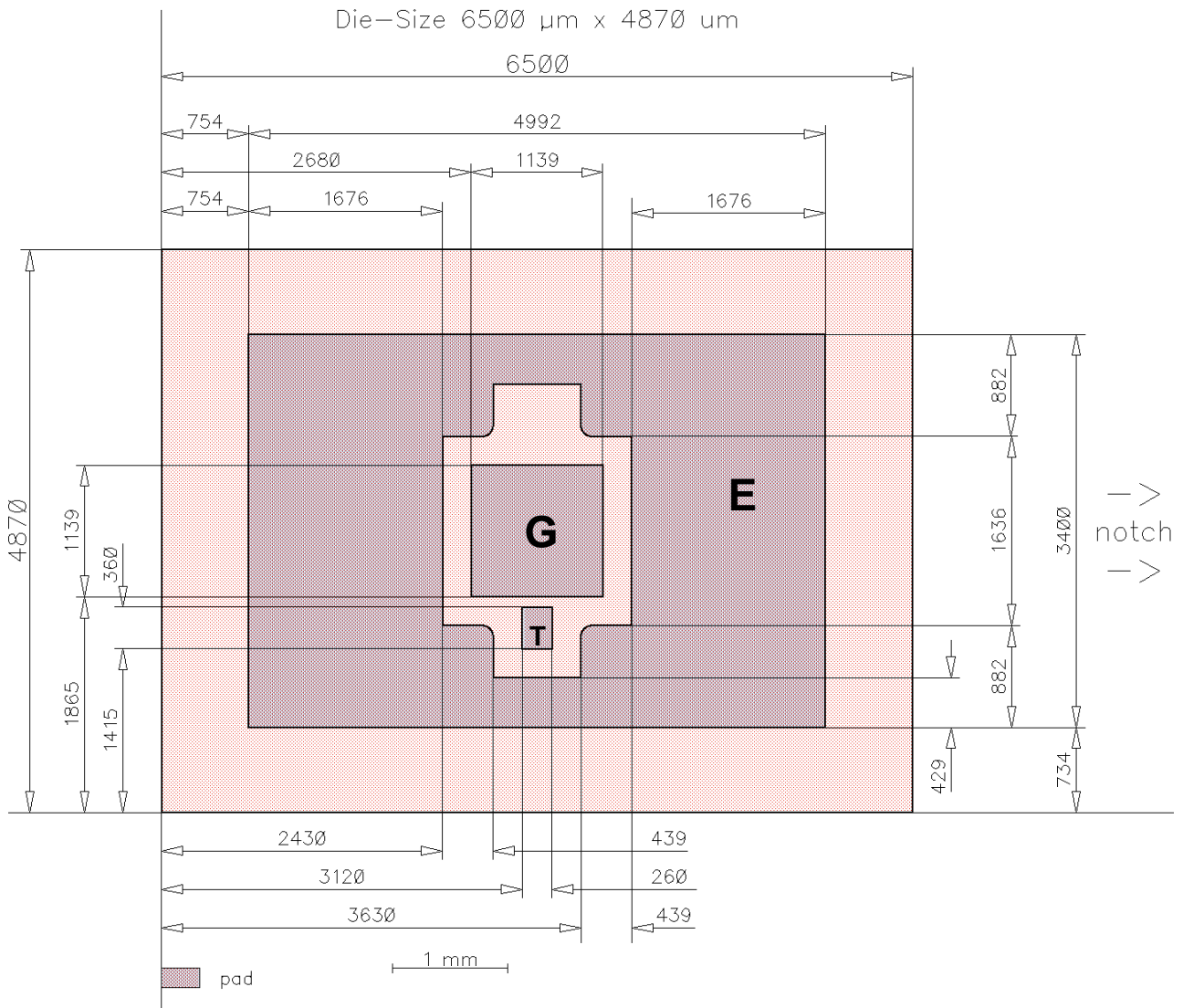
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Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Application example	FP25R12KE3	Rev. 3.2
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Chip Drawing



E = Emitter

G = Gate

T = Test pad do not contact



SIGC32T120R3E

Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Revision	Subjects (major changes since last revision)	Date
2.2	Wafer diameter change to 200mm	06.07.2010
2.3	Additional Basic Types L7641M, L7641T, L7641E	27.06.2014
2.4	Editorial changes, V_{CEsat} at 125°C, chip drawing	05.02.2016

Relevant Application Notes

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